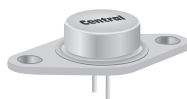


2N6211
2N6212
2N6213

**SILICON
PNP POWER TRANSISTORS**



TO-66 CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6211, 2N6212, and 2N6213 are silicon PNP transistors designed for high speed switching and high voltage amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Peak Collector Current
Continuous Base Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	2N6211	2N6212	2N6213	UNITS
V_{CBO}	275	350	400	V
V_{CEO}	225	300	350	V
V_{EBO}		6.0		V
I_C		2.0		A
I_{CM}		5.0		A
I_B		1.0		A
P_D		35		W
T_J, T_{stg}		-65 to +200		$^\circ\text{C}$
θ_{JC}		5.0		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6211		2N6212		2N6213		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=250\text{V}, V_{BE}=1.5\text{V}$	-	0.5	-	-	-	-	mA
I_{CEV}	$V_{CE}=315\text{V}, V_{BE}=1.5\text{V}$	-	-	-	0.5	-	-	mA
I_{CEV}	$V_{CE}=360\text{V}, V_{BE}=1.5\text{V}$	-	-	-	-	-	0.5	mA
I_{CEV}	$V_{CE}=250\text{V}, V_{BE}=1.5\text{V}, T_C=100^\circ\text{C}$	-	5.0	-	-	-	-	mA
I_{CEV}	$V_{CE}=315\text{V}, V_{BE}=1.5\text{V}, T_C=100^\circ\text{C}$	-	-	-	5.0	-	-	mA
I_{CEV}	$V_{CE}=360\text{V}, V_{BE}=1.5\text{V}, T_C=100^\circ\text{C}$	-	-	-	-	-	5.0	mA
I_{CEO}	$V_{CE}=150\text{V}$	-	5.0	-	5.0	-	5.0	mA
I_{EBO}	$V_{EB}=6.0\text{V}$	-	1.0	-	0.5	-	0.5	mA
BV_{CEV}	$I_C=50\text{mA}, V_{BE}=1.5\text{V}, L=10\text{mH}$	275	-	350	-	400	-	V
BV_{CER}	$I_C=50\text{mA}, R_{BE}=50\Omega$	250	-	325	-	375	-	V
BV_{CEO}	$I_C=50\text{mA}$	225	-	300	-	350	-	V
BV_{EBO}	$I_E=1.0\text{mA}$	6.0	-	-	-	-	-	V
BV_{EBO}	$I_E=0.5\text{mA}$	-	-	6.0	-	6.0	-	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=125\text{mA}$	-	1.4	-	1.6	-	2.0	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=125\text{mA}$	-	1.4	-	1.4	-	1.4	V
h_{FE}	$V_{CE}=2.8\text{V}, I_C=1.0\text{A}$	10	100	-	-	-	-	
h_{FE}	$V_{CE}=3.2\text{V}, I_C=1.0\text{A}$	-	-	10	100	-	-	
h_{FE}	$V_{CE}=4.0\text{V}, I_C=1.0\text{A}$	-	-	-	-	10	100	

R3 (11-November 2015)

2N6211
2N6212
2N6213

SILICON
PNP POWER TRANSISTORS

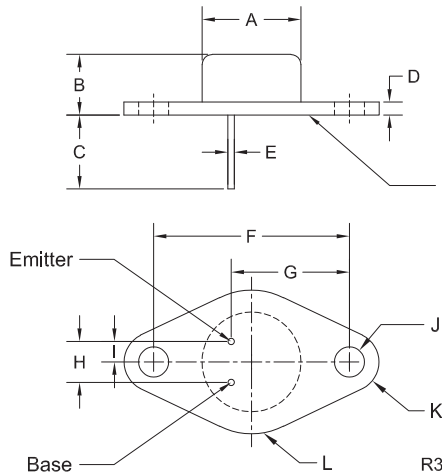


ELECTRICAL CHARACTERISTICS - Continued: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10\text{V}$, $I_C=200\text{mA}$, $f=5.0\text{MHz}$	20		MHz
C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1.0\text{MHz}$		220	pF
t_r	$V_{CC}=200\text{V}$, $I_C=1.0\text{A}$, $I_{B1}=I_{B2}=125\text{mA}$		0.6	μs
t_s	$V_{CC}=200\text{V}$, $I_C=1.0\text{A}$, $I_{B1}=I_{B2}=100\text{mA}$		2.5	μs
t_f	$V_{CC}=200\text{V}$, $I_C=1.0\text{A}$, $I_{B1}=I_{B2}=125\text{mA}$		0.6	μs
$I_{S/b}^*$	$V_{CE}=40\text{V}$	875		mA

*Pulsed: 1.0s non-repetitive pulse.

TO-66 CASE - MECHANICAL OUTLINE



Seating Plane:
The seating plane must be within 0.001" concave to 0.004" convex within 0.600" diameter from the center of the device.

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.470	0.500	11.94	12.70
B	0.250	0.340	6.35	8.64
C	0.360	-	9.14	-
D	0.050	0.075	1.27	1.91
E (DIA)	0.028	0.034	0.71	0.86
F	0.956	0.964	24.28	24.48
G	0.570	0.590	14.48	14.99
H	0.190	0.210	4.83	5.33
I	0.093	0.107	2.36	2.72
J (DIA)	0.142	0.152	3.61	3.86
K (RAD)	0.141		3.58	
L (RAD)	0.345		8.76	

TO-66 (REV:R3)

MARKING:
FULL PART NUMBER

R3 (11-November 2015)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

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